

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Akio KITAMURA

Group Art Unit: 2815

Serial No.: 10/055,722

Examiner: J. Fenty

Filed: January 23, 2002

Attorney Docket No.: FUJI:203

For: SEMICONDUCTOR INTEGRATED CIRCUIT AND MANUFACTURING METHOD THEREFORE

Assistant Commissioner for Patents
Washington, D.C. 20231

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Sir:

Enclosed herewith are:

Amendment & Request for Reconsideration: 4 Pages

Total Including this Cover Sheet: 5 Pages

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AMENDMENT & REQUEST FOR RECONSIDERATION

Sir:

In reply to the November 20, 2002 Office Action, this application has been amended as indicated below. A marked up version showing the incorporated changes is attached. No fee is due.

IN THE CLAIMS:

*Kindly cancel non-elected claims 9 and 10 without prejudice or disclaimer.**Kindly replace claims 1 and 8 with the following corresponding replacement claims:*

--1. (Amended) A semiconductor integrated circuit device comprising:

a semiconductor substrate;

a first lateral MOS transistor and a second lateral MOS transistor integrated in the semiconductor substrate, wherein said second lateral MOS transistor has a lower threshold voltage than said first lateral MOS transistor and said first lateral MOS transistor has a smaller channel length than said second lateral MOS transistor; and